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## **CMOS SERIAL E<sup>2</sup>PROM**

# S-29453A

The S-29453A Series is high speed, low power 8K-bit serial E2PROM with a wide operating voltage range. It is organized as 512-word×16-bit. It is capable of sequential read, where addresses are automatically incremented in 16-bit blocks. The instruction code is compatible with the M6M800X1 Series.

Endurance: 105 cycles/word

Data retention: 10 years

#### ■ Features

• Low power consumption

Standby : 1  $\mu$ A Max.

Operating : 1.2 mA Max. ( $V_{\text{CC}}$ =5.5 V)

0.4 mA Max. (V<sub>CC</sub>=2.5 V)

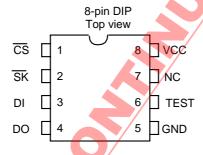
Wide operating voltage range
 Write : 2.5 to 5.5 V
 Read : 1.8 to 5.5 V

· Sequential read capable

#### ■ Package

8-pin DIP (PKG drawing code : DP008-A)8-pin SOP (PKG drawing code : FE008-A)

## ■ Pin Assignment



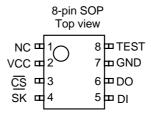
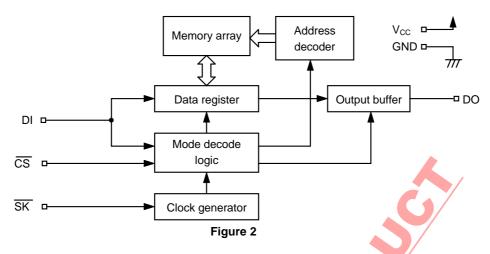


Figure 1

<u>cs</u>	Chip select input
SK	Serial clock input
DI	Serial data input
DO	Serial data output
GND	Ground (0 V)
VCC	Power supply
TEST	Test pin (normally kept open) (can be connected to GND or Vcc)

## **■** Block Diagram



## **■ Instruction Set**

Table 1

Instruction	Operation block	Address	Data
READ (Read data)	1010100A <sub>8</sub>	A <sub>7</sub> to A <sub>0</sub>	D <sub>15</sub> to D <sub>0</sub> output <sup>*</sup>
PROGRAM (Write data)	1010010A <sub>8</sub>	A <sub>7</sub> to A <sub>0</sub>	D <sub>15</sub> to D <sub>0</sub>
EWEN (Program enable)	10100011	xxxxxxxx	_
EWDS (Program disable)	10100000	xxxxxxx	_

x : Doesn't matter.

\* : When 16-bit data of the specified address is output, the data of the next address is

## ■ Absolute Maximum Ratings

Table 2

Parameter	Symbol	Ratings	Unit
Power supply voltage	$V_{CC}$	-0.3 to +7.0	V
Input voltage	$V_{IN}$	-0.3 to V <sub>CC</sub> +0.3	٧
Output voltage	$V_{OUT}$	-0.3 to $V_{\text{CC}}$	٧
Storage temperature under bias	T <sub>bias</sub>	-50 to +95	°C
Storage temperature	$T_{stg}$	-65 to +150	°C

## **■** Recommended Operating Conditions

Table 3

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Danisa	\ /	Read Operation	1.8		5.5	V
Power supply voltage	$V_{CC}$	Write Operation	2.5	_	5.5	٧
High level innet caltern	\/	V <sub>CC</sub> =2.5 to 5.5V	0.8×V <sub>CC</sub>		V <sub>CC</sub>	V
High level input voltage	V <sub>IH</sub>	V <sub>CC</sub> =1.8 to 2.5V	0.8×V <sub>CC</sub>		V <sub>CC</sub>	V
Laurianalian dualta aa	\ /	V <sub>CC</sub> =2.5 to 5.5V	0.0		0.2×V <sub>CC</sub>	٧
Low level input voltage	V <sub>IL</sub>	V <sub>CC</sub> =1.8 to 2.5V	0.0	-	0.15×V <sub>CC</sub>	٧
Operating temperature	$T_{opr}$		-40		<b>/</b> +85	°C

## **■ DC Electrical Characteristics**

#### Table 4

Parameter	Symbol	Conditions	V <sub>CC</sub> =	=5.0 V±	10 %	V <sub>CC</sub> =	2.5 to 3	3.3 V	V <sub>CC</sub> =	=1.8 to 2	2.5 V	Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Offic
Current consumption (READ)	I <sub>CC1</sub>	DO unloaded	-	_	1.2			0.5	-	-	0.4	mA
Current consumption (PROGRAM)	I <sub>CC2</sub>	DO unloaded	_	_	5.0	7	_	2.0	_	_	_	mA

Parameter	Symbol	Conditions	V <sub>CC</sub> =5	.0 V±1	0%	V <sub>CC</sub> =2	.5 to 4	.5 V	V <sub>CC</sub> =1	.8 to 2	.5 V	Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Offic
Standby current consumption	I <sub>SB</sub>	Input: V <sub>CC</sub> or GND		#	1.0			1.0			1.0	μА
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> =GND to V <sub>CC</sub>		0.1	1.0		0.1	1.0		0.1	1.0	μА
Output leakage current	I <sub>LO</sub>	V <sub>OUT</sub> =GND to V <sub>CC</sub>	<b>/</b>	0.1	1.0	_	0.1	1.0		0.1	1.0	μА
Low level output	V <sub>OL</sub>	CMOS I <sub>OL</sub> =100 μA	/ —		0.1			0.1			0.1	V
voltage	V OL	TTL I <sub>OL</sub> =2.1 mA			0.45							V
High level output voltage	V <sub>он</sub>	CMOS V <sub>CC</sub> =2.5 to 5.5 V : I <sub>OH</sub> =-100 μA V <sub>CC</sub> =1.8 to 2.5 V : I <sub>OH</sub> =-10 μA	V <sub>CC</sub> -0.7			V <sub>CC</sub> -0.7			V <sub>CC</sub> -0.3			<b>V</b>
		TTL, I <sub>OH</sub> =-400 μA	2.4	_			_					V
Write enable latch data hold voltage	$V_{DH}$		1.5	_	_	1.5	_		1.5			٧

## **■** Endurance

## Table 6

	Parameter	Symbol	Min.	Тур.	Max.	Unit
<u>//</u>	Endurance	$N_W$	10 <sup>5</sup>		_	cycles/word

## ■ Pin Capacitance

#### Table 7

(Ta=25°C, f=1.0 MHz, V<sub>CC</sub>=5 V)

			(			100 0 17
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>IN</sub>	V <sub>IN</sub> =0 V			8	pF
Output Capacitance	Сопт	V <sub>OUT</sub> =0 V	_	_	10	PΓ

## ■ AC Electrical Characteristics

Table 8 Measuring conditions

Input pulse voltage	0.1×V <sub>CC</sub> to 0.9×V <sub>CC</sub>
Output reference voltage	0.5×V <sub>CC</sub>
Output load	100pF

Table 9

			Rea	d/Write	opera	tions		Rea	d opera	ation	
Parameter	Symbol	V <sub>CC</sub> =	5.0 V±	10 %	V <sub>CC</sub> =	2.5 to	4.5 V	Vcc=	1.8 to	2.5 V	Unit
		Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	∕Max.	
CS setup time	t <sub>CSS</sub>	0.2			0.4	_		1.0			μS
CS hold time	t <sub>CSH</sub>	0.2			0.4			1.0			μS
CS setup time (CPU)	t <sub>CSS (CPU)</sub>	0.2		-	0.4	_		1.0			μS
CS hold time (CPU)	t <sub>CSH (CPU)</sub>	0.2		-	0.4	_		1.0			μS
CS deselect time	t <sub>CDS</sub>	0.2			0.2		b	0.4			μS
Data setup time	t <sub>DS</sub>	0.2			0.4			0.8			μS
Data hold time	t <sub>DH</sub>	0.2			0.4	1	<b>)</b>	0.8			μS
1 data output delay time	t <sub>PD1</sub>			0.4	1	L	0.8			2.0	μS
0 data output delay time	t <sub>PD0</sub>			0.4	4	1	0.8			2.0	μS
Clock frequency	f <sub>SK</sub>	0.0		2.0	0.0		0.5	0.0		0.2	MHz
Clock pulse width	t <sub>SKH</sub> , t <sub>SKL</sub>	0.25			1.0			2.5			μS
Output disable time	$t_{HZ1}, t_{HZ2}$	0	50	150	0	500	1000				ns
Output enable time	t <sub>SV</sub>	0	50	150	0	500	1000				ns
Programming time	t <sub>PR</sub>		4.0	10/		4.0	10				ms

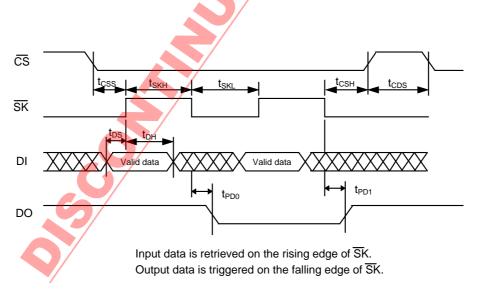


Figure 3 Timing Chart

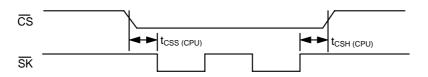


Figure 4 Timing Chart for  $t_{\text{CSS (CPU)}}$  and  $t_{\text{CSH (CPU)}}$  when CPU is connected

#### ■ Operation

Instructions (in the order of operation code, address, and data) are latched to DI in synchronization with the rising edge of  $\overline{SK}$  after  $\overline{CS}$  goes low. A start-bit can only be recognized when the high of DI is latched at the rising edge of  $\overline{SK}$  after changing  $\overline{CS}$  to low, it is impossible for it to be recognized as long as DI is low, even if there are  $\overline{SK}$  pulses after  $\overline{CS}$  goes low. Instruction finishes when  $\overline{CS}$  goes high, where it must be high between commands during  $t_{CDS}$ .

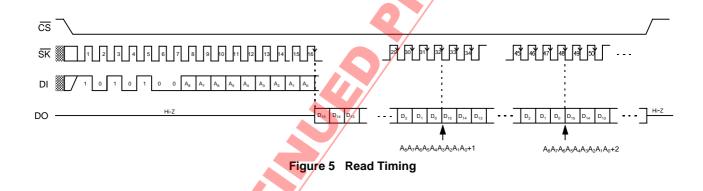
All input, including DI and  $\overline{SK}$  signals, is ignored while  $\overline{CS}$  is high. The operation code plus address is a multiple of 8-bits. This makes it easy to prepare your own software using a serial interface incorporated into the CPU.

#### 1. READ

The READ instruction reads data from a specified address. The READ operation code and address are continuously latched in synchronization with the rising edge of SK. The DO pin begins to output at the 16-th clock from a start-bit. Data is continuously output in synchronization with the falling edge of SK.

When all of the data  $(D_{15}$  to  $D_0)$  in the specified address has been read, data in the next address can be read with the input of another SK clock. Thus, the data over whole area of the memory can be read by continuously inputting SK clocks as long as  $\overline{CS}$  is low.

The last address (An  $\cdot \cdot \cdot$  A1 A0 = 1  $\cdot \cdot \cdot$  11) rolls over to the top address (An  $\cdot \cdot \cdot$  A1 A0 = 0  $\cdot \cdot \cdot$  00).



Seiko Instruments Inc.

# CMOS SERIAL E<sup>2</sup>PROM S-29453A

#### 2. PROGRAM

The PROGRAM instruction writes 16-bit data to a specified address.

After changing  $\overline{CS}$  to low, input PROGRAM operation code, address, and 16-bit data. If there is a data overflow of more than 16 bits, only the last 16-bits of the data is considered valid. Changing  $\overline{CS}$  to high will start the PROGRAM operation. It is not necessary to make the data "1" before initiating the PROGRAM operation.

The write operation is completed in 10 ms ( $t_{PR}$  Max.), and the typical write period is less than 5 ms. In the S-29453A, it is easy to VERIFY the completion of the write operation in order to minimize the write cycle by setting  $\overline{CS}$  to "L" and checking the DO pin after the write operation begins by setting  $\overline{CS}$  to "H" VERIFY operations to detect changes in the DO output can be executed in succession. One is a change from "L" to "H" with  $\overline{CS}$ ="L" The other is a change from "L" to "H" after setting  $\overline{CS}$  to "L" and returning  $\overline{CS}$  to "H" repeatedly.

Because all  $\overline{SK}$  and DI inputs are ignored during the write operation, any input of instruction will also be disregarded. When DO outputs high after completion of the write operation or if it is in the high-impedence state (Hi-Z), the input of instructions is available. Even if the DO pin remains high, it will enter the high-impedence state upon the recognition of a high of DI attached to the rising edge of an  $\overline{SK}$  pulse.

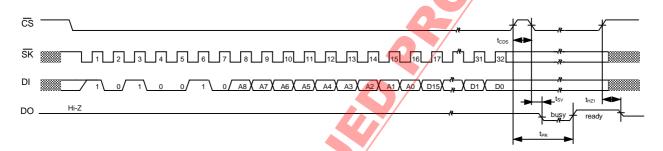


Figure 6 PROGRAM Timing

#### 3. Write enable (EWEN) and Write disable (EWDS)

The EWEN instruction puts the S-29453A into write enable mode, which accepts PROGRAM instruction. The EWDS instruction puts the S-29453A into write disable mode, which refuses PROGRAM instruction.

The S-29453A powers on in write disable mode, which protects data against unexpected, erroneous write operations caused by noise and/or CPU malfunctions. It should be kept in write disable mode except when performing write operations.

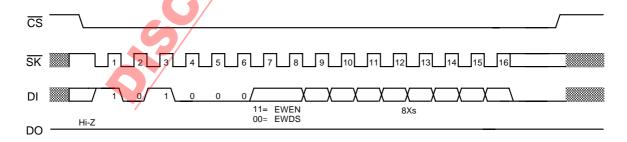


Figure 7 EWEN/EWDS Timing

#### ■ Receiving a Start-Bit

A start-bit can be recognized by latching the high level of DI at the rising edge of  $\overline{SK}$  after changing  $\overline{CS}$  to low. The write operation begins by inputting the write instruction and setting  $\overline{CS}$  to high. The DO pin then outputs low during the write operation and high at its completion by setting  $\overline{CS}$  to low (Verify Operation). Therefore, only after a write operation, in order to accept the next command by having  $\overline{CS}$  go low, the DO pin is switched from a state of high-impedence to a state of data output; but if it recognizes a start-bit, the DO pin returns to a state of high-impedence (see Figure 8).

Make sure that data output from the CPU does not interfere with the data output from the serial memory IC when you configure a 3-wire interface by connecting DI input pin and DO output pin. Such interference may cause a start-bit fetch problem.

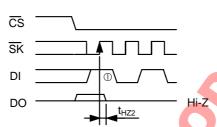


Figure 8 Start-Bit latching timing

### ■ Three-Wire Interface (DI-DO direct connection)

Although the normal configuration of a serial interface is a 4-wire interface to CS, SK, DI, and DO, a 3-wire interface is also a possibility by connecting DI and DO. However, since there is a possibility that the DO output from the serial memory IC will interfere with the data output from the CPU with a 3-wire interface, install a resistor between DI and DO in order to give preference to data output from the CPU to DI(See Figure 9).

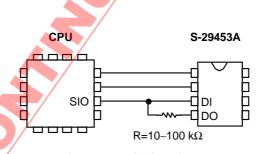
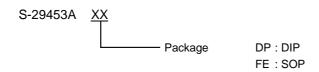
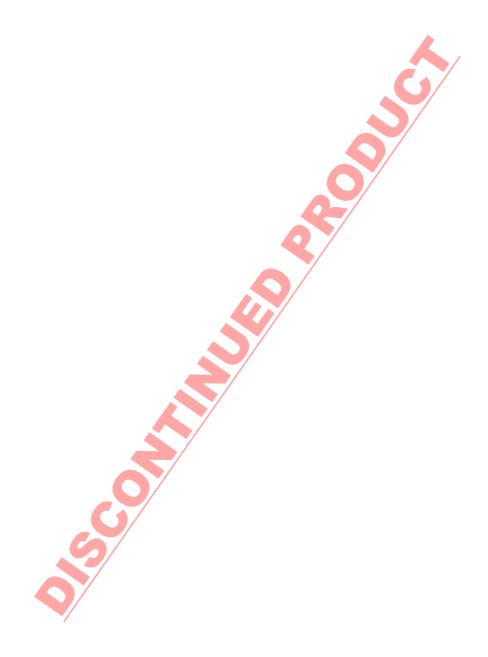


Figure 9 3-wire interface

•Please refer Application Note "S-29 & S-93C series EEPROMs Tips, Tricks & Traps" for equivalent circuit of each pin.

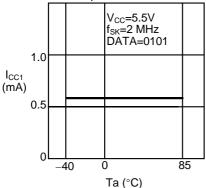
### ■ Ordering Information



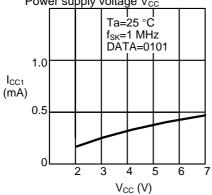


#### ■ Characteristics

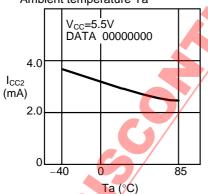
- 1. DC Characteristics
  - 1.1 Current consumption (READ) I<sub>CC1</sub> Ambient temperature Ta



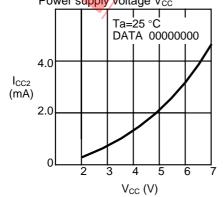
1.3 Current consumption (READ)  $I_{CC1}$  - Power supply voltage  $V_{CC}$ 



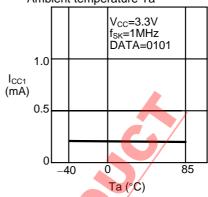
1.5 Current consumption (PROGRAM) I<sub>CC2</sub> - Ambient temperature Ta



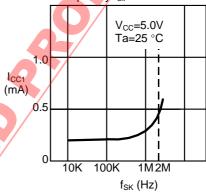
1.7 Current consumption (PROGRAM)  $I_{CC2}$  - Power supply voltage  $V_{CC}$ 



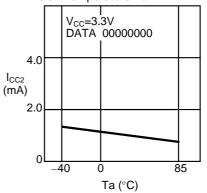
1.2 Current consumption (READ) I<sub>CC1</sub> - Ambient temperature Ta



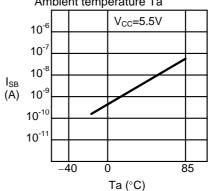
1.4 Current consumption (READ) I<sub>CC1</sub> - Clock frequency f<sub>sk</sub>



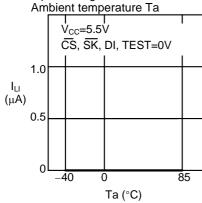
 Current consumption (PROGRAM) I<sub>CC2</sub> -Ambient temperature Ta



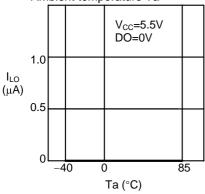
1.8 Standby current consumption I<sub>SB</sub> -- Ambient temperature Ta



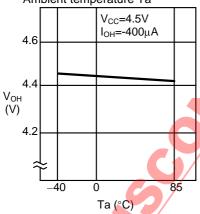
1.9 Input leakage current I<sub>LI</sub> -



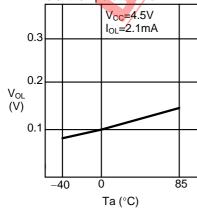
1.11 Output leakage current I<sub>LO</sub> - Ambient temperature Ta



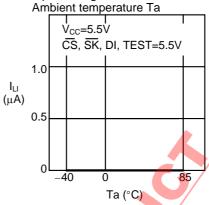
1.13 High level output voltage V<sub>OH</sub> - Ambient temperature Ta



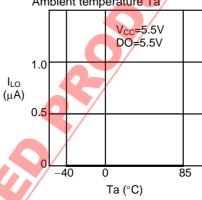
1.15 Low level output voltage V<sub>OL</sub> - Ambient temperature Ta



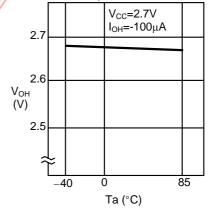
1.10 Input leakage current I<sub>LI</sub> -



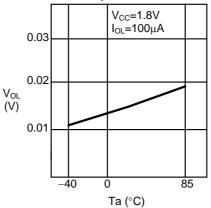
1.12 Output leakage current Lo Ambient temperature Ta



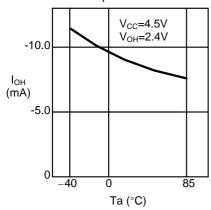
1.14 High level output voltage V<sub>OH</sub> - Ambient temperature Ta



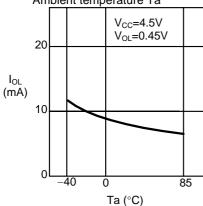
1.16 Low level output voltage V<sub>OL</sub>-Ambient temperature Ta



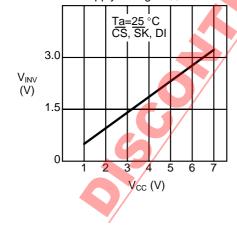
1.17 High level output current I<sub>OH</sub> - Ambient temperature Ta



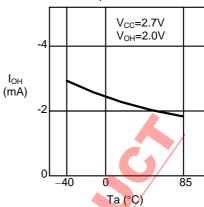
1.19 Low level output current  $I_{OL}$ -Ambient temperature Ta



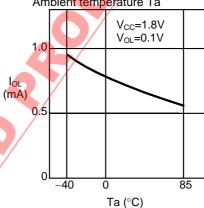
1.21 Input inversion voltage  $V_{\text{INV}}$  - Power supply voltage  $V_{\text{CC}}$ 



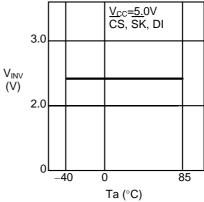
1.18 High level output current I<sub>OH</sub> - Ambient temperature Ta



1.20 Low level output current I<sub>OL</sub> - Ambient temperature Ta



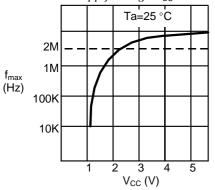
 $\begin{array}{c} \text{1.22 Input inversion voltage $V_{\text{INV}}$ -} \\ \text{Ambient temperature Ta} \end{array}$ 



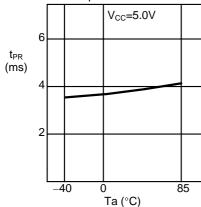
# CMOS SERIAL E<sup>2</sup>PROM S-29453A

### 2. AC Characteristics

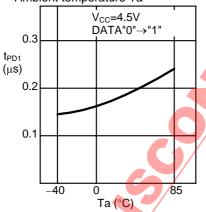
2.1 Maximum operating frequency  $f_{\text{max}}$  - Power supply voltage  $V_{\text{CC}}$ 



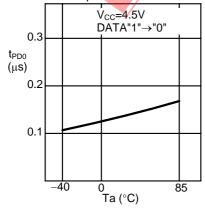
2.3 Program time t<sub>PR</sub> - Ambient temperature Ta



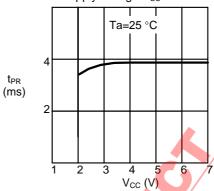
2.5 "1" Data output delay time  $t_{\text{PD1}}$  - Ambient temperature Ta



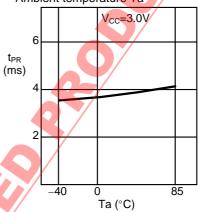
2.7 "0" Data output delay time t<sub>PD0</sub> - Ambient temperature Ta



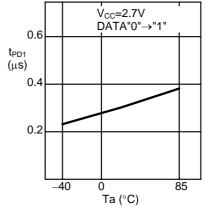
2.2 Program time  $t_{PR}$  - Power supply voltage  $V_{CC}$ 



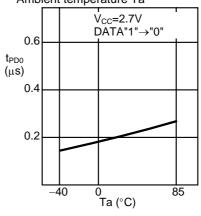
2.4 Program time t<sub>PR</sub> - Ambient temperature Ta



2.6 "1"Data output delay time t<sub>PD1</sub> - Ambient temperature Ta



2.8 "0" Data output delay time  $t_{\text{PD0}}$  - Ambient temperature Ta



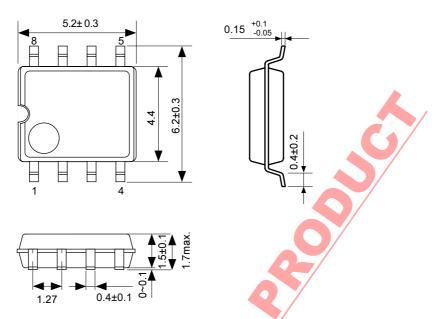
# ■ 8-Pin SOP

## **FE008-A Rev.1.0** 020128

## Dimensions

Unit:mm

No.: FE008-A-R-SD-1.0

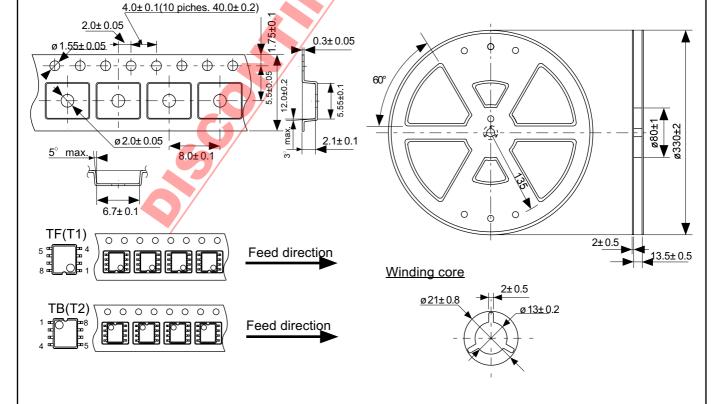


No.: FE008-A-P-SD-1.0

# Taping Specifications

## Reel Specifications

1 reel holds 2000 ICs.



No.: FE008-A-C-SD-3.0



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